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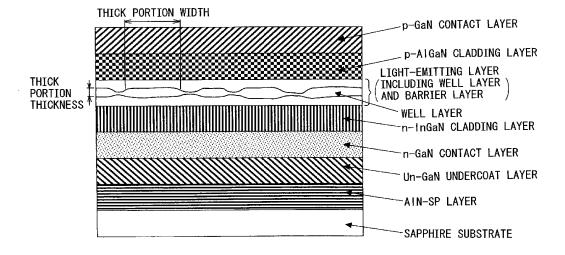
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(54) Title: GALLIUM NITRIDE-BASED COMPOUND SEMICONDUCTOR MULTILAYER STRUCTURE AND PRODUC-TION METHOD THEREOF



(57) Abstract: An object of the present invention is to provide a gallium nitride compound semiconductor multilayer structure useful for producing a gallium nitride compound semiconductor light-emitting device which operates at low voltage while maintaining satisfactory light emission output. The inventive gallium nitride compound semiconductor multilayer structure comprises a substrate, and an n-type layer, a light-emitting layer, and a p-type layer formed on the substrate, the light-emitting layer having a multiple quantum well structure in which a well layer and a barrier layer are alternately stacked repeatedly, said light-emitting layer being sandwiched by the n-type layer and the p-type layer, wherein the well layer comprises a thick portion and a thin portion, and the barrier layer contains a dopant.



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